

## 1. General description

Planar passivated four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance.

## 2. Features and benefits

- High blocking voltage capability
- High noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

## 3. Applications

- General purpose motor control
- General purpose switching

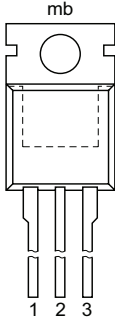
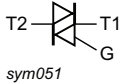
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values				Unit
Absolute maximum rating							
V <sub>DRM</sub>	repetitive peak off-state voltage		600				V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 91 °C; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	25				A
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 20 ms; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	190				A
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>		-	6	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>		-	10	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>		-	11	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>		-	23	70	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA140-600	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

7. Marking

Table 4. Marking codes

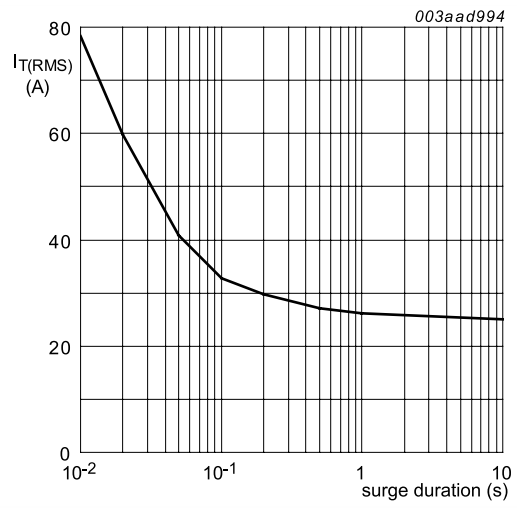
Type number	Marking codes
BT140-600	BT140-600

## 8. Limiting values

**Table 5. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Values	Unit
$V_{\text{DRM}}$	repetitive peak off-state voltage		600	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{mb}} \leq 91^{\circ}\text{C}$ ; <a href="#">Fig 1</a> ; <a href="#">Fig 2</a> ; <a href="#">Fig 3</a>	25	A
$I_{\text{TSM}}$	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25^{\circ}\text{C}$ ; $t_{\text{p}} = 20 \text{ ms}$ ; <a href="#">Fig 4</a> ; <a href="#">Fig 5</a>	190	A
		full sine wave; $T_{\text{j(init)}} = 25^{\circ}\text{C}$ ; $t_{\text{p}} = 16.7 \text{ ms}$	209	A
$I^2t$	$I^2t$ for fusing	$t_{\text{p}} = 10 \text{ ms}$ ; SIN	180	$\text{A}^2\text{s}$
$dI_{\text{T}}/dt$	rate of rise of on-state current	$I_{\text{G}} = 70 \text{ mA}$ ; T2+ G+	50	$\text{A}/\mu\text{s}$
		$I_{\text{G}} = 70 \text{ mA}$ ; T2+ G-	50	$\text{A}/\mu\text{s}$
		$I_{\text{G}} = 70 \text{ mA}$ ; T2- G-	50	$\text{A}/\mu\text{s}$
		$I_{\text{G}} = 140 \text{ mA}$ ; T2- G+	10	$\text{A}/\mu\text{s}$
$I_{\text{GM}}$	peak gate current		2	A
$P_{\text{GM}}$	peak gate power		5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	0.5	W
$T_{\text{stg}}$	storage temperature		-40 to 150	$^{\circ}\text{C}$
$T_{\text{j}}$	junction temperature		125	$^{\circ}\text{C}$



$f = 50 \text{ Hz}; T_{mb} = 91^\circ \text{C}$

Fig. 1. RMS on-state current as a function of surge duration; maximum values

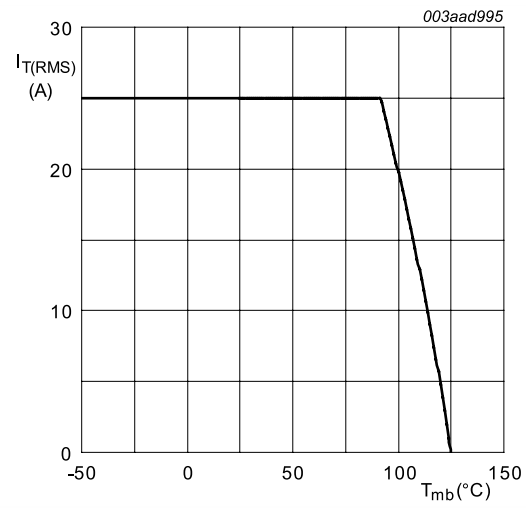


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

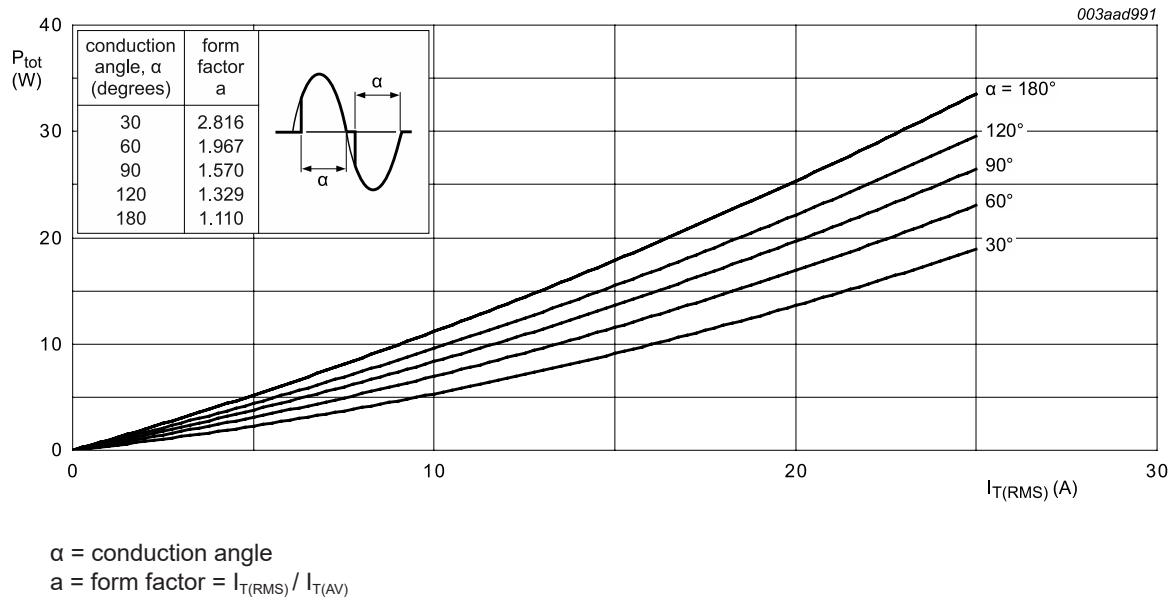


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

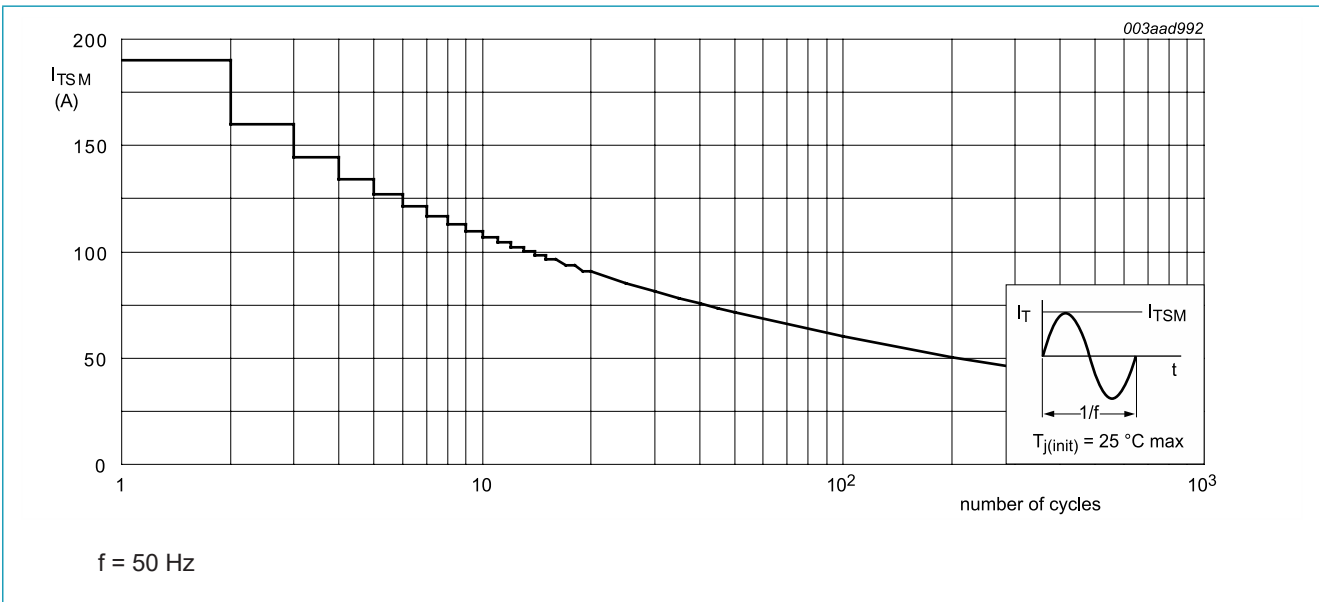


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

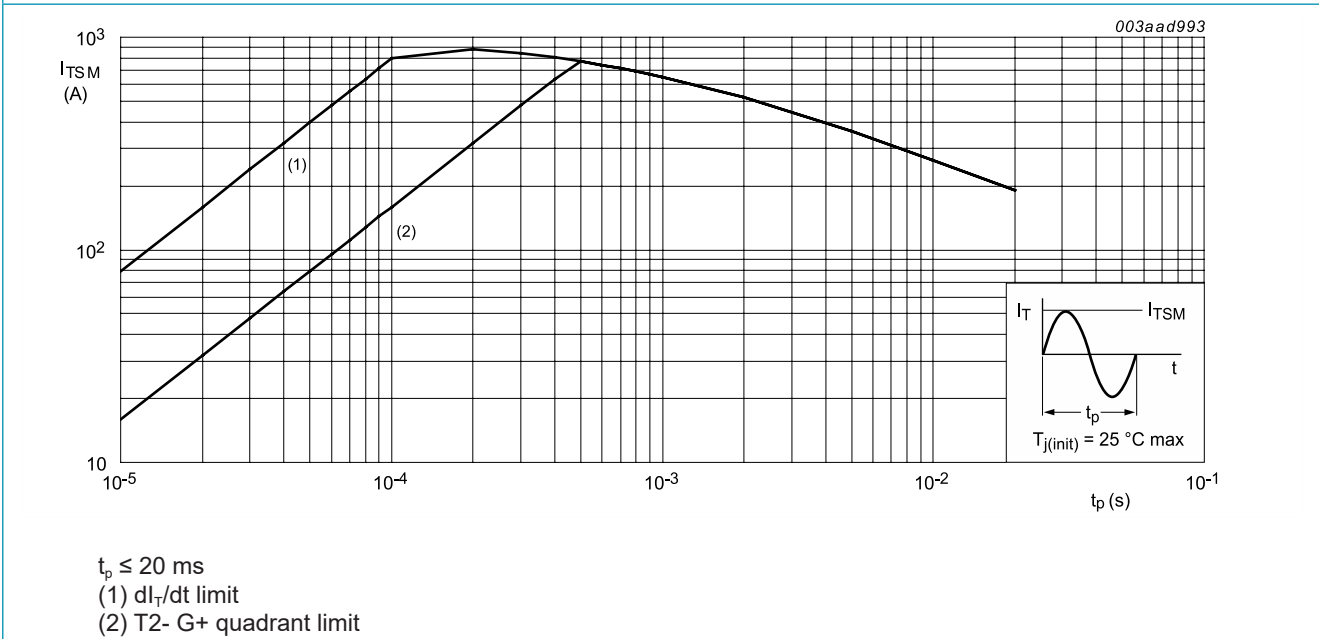
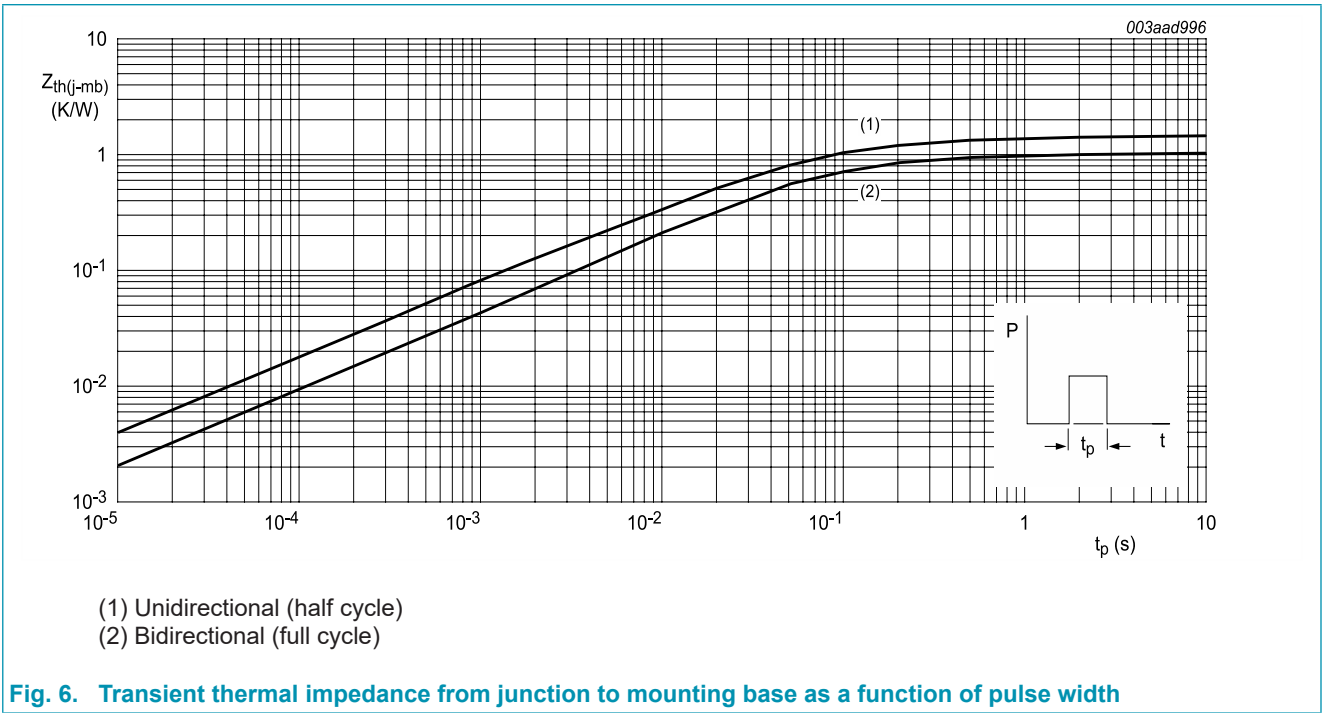


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

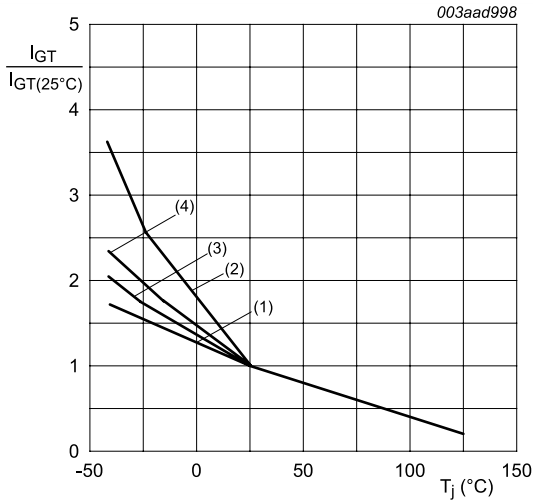
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; Fig.6		-	-	1	K/W
		half cycle; Fig.6		-	-	1.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	60	-	K/W



## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
<b>Static characteristics</b>							
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>		-	6	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>		-	10	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>		-	11	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>		-	23	70	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>		-	8	40	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>		-	30	60	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>		-	18	40	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G+; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>		-	15	60	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; T2+; <a href="#">Fig. 9</a>		-	7	60	mA
		$V_D = 12\text{ V}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; T2-; <a href="#">Fig. 9</a>			12	60	mA
$V_T$	on-state voltage	$I_T = 30\text{ A}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>		-	1.3	1.55	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>		-	0.7	1	V
		$V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_J = 125\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>		0.25	0.4	-	V
$I_D$	off-state current	$V_D = 600\text{ V}$ ; $T_J = 125\text{ }^\circ\text{C}$		-	0.1	0.5	mA
<b>Dynamic characteristics</b>							
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$ ; $T_J = 125\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit		100	300	-	V/ $\mu\text{s}$
$dV_{com}/dt$	rate of change of commutating voltage	$V_D = 400\text{ V}$ ; $T_J = 95\text{ }^\circ\text{C}$ ; $dI_{com}/dt = 9\text{ A/ms}$ ; $I_T = 25\text{ A}$ ; gate open circuit		-	10	-	V/ $\mu\text{s}$
$t_{gt}$	gate-controlled turn-on time	$I_{TM} = 30\text{ A}$ ; $V_D = 600\text{ V}$ ; $I_G = 0.1\text{ A}$ ; $dI_G/dt = 5\text{ A}/\mu\text{s}$		-	2	-	$\mu\text{s}$



- (1) T2+ G+
- (2) T2+ G-
- (3) T2- G-
- (4) T2- G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

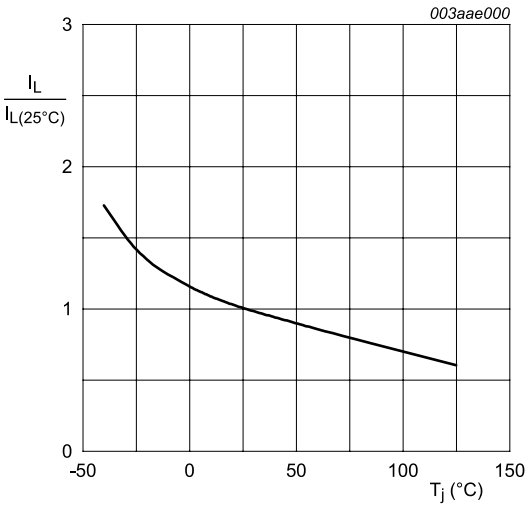


Fig. 8. Normalized latching current as a function of junction temperature

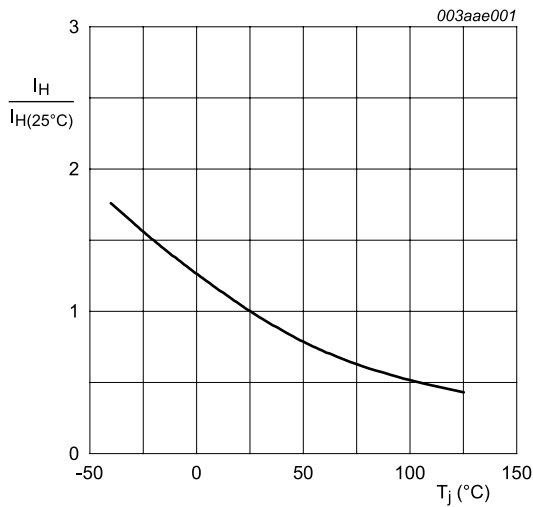
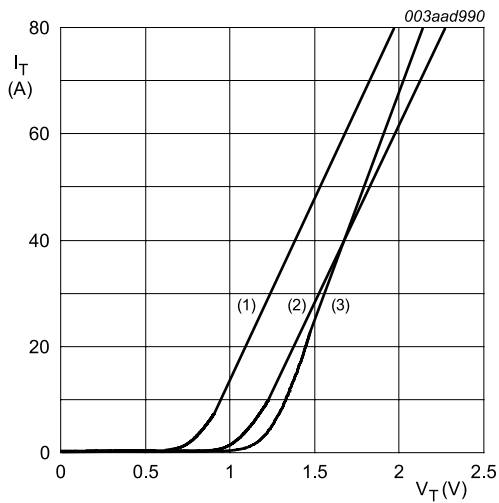


Fig. 9. Normalized holding current as a function of junction temperature



- $V_o = 1.073 \text{ V}; R_s = 0.015 \Omega$
- (1)  $T_j = 125^{\circ}\text{C}$ ; typical values
  - (2)  $T_j = 125^{\circ}\text{C}$ ; maximum values
  - (3)  $T_j = 25^{\circ}\text{C}$ ; maximum values

Fig. 10. On-state current as a function of on-state voltage



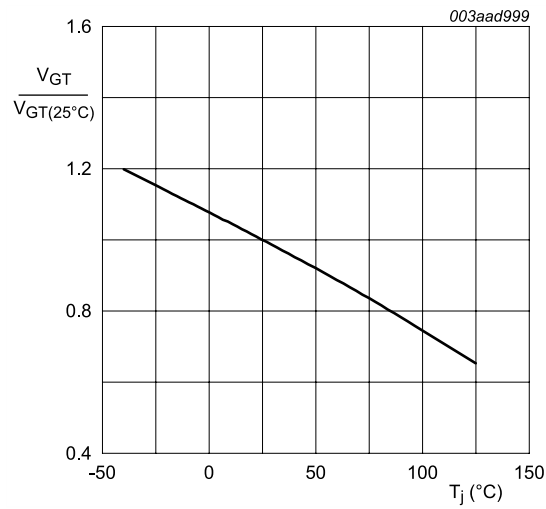
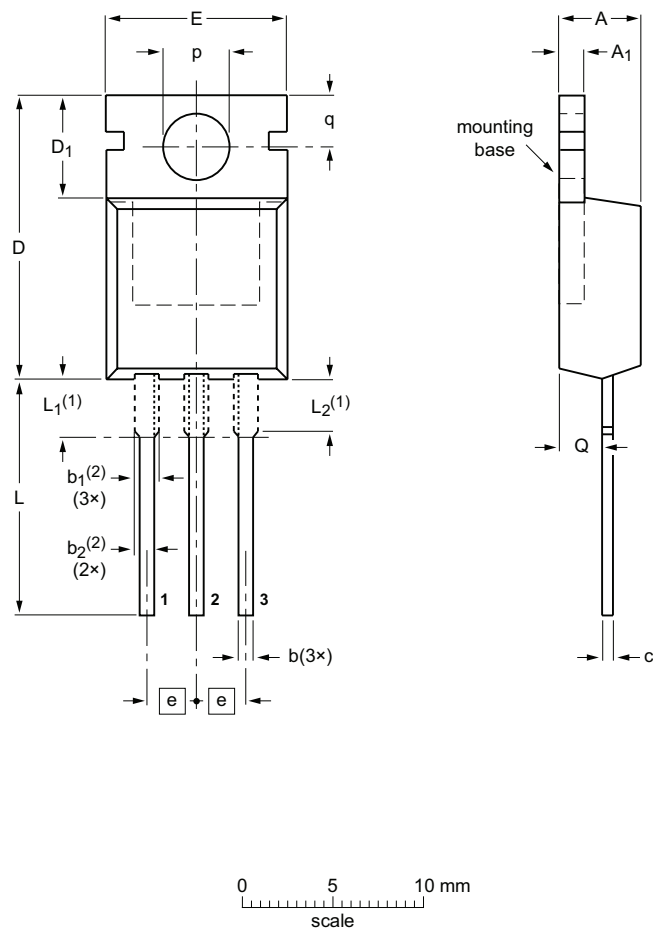


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub> (2)	b <sub>2</sub> (2)	c	D	D <sub>1</sub>	E	e	L	L <sub>1</sub> (1)	L <sub>2</sub> (1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 22 March 2018



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